

SPOC - BTS5461SF

SPI Power Controller
For Advanced Front Light Control

Data Sheet

Rev. 1.0, 2011-11-17

Automotive Power



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For Advanced Front Light Control SPI Power Controller

SPOC - BTS5461SF





1 Overview

Features

- · 8 bit serial peripheral interface for control and diagnosis
- 3.3 V and 5 V compatible logic pins
- · Very low stand-by current
- Enhanced electromagnetic compatibility (EMC) for bulbs as well as LEDs with increased slew rate
- · Stable behavior at under voltage
- Device ground independent from load ground
- Green Product (RoHS-Compliant)
- AEC Qualified



PG-DSO-36-43

Description

The SPOC - BTS5461SF is a four channel high-side smart power switch in PG-DSO-36-43 package providing embedded protective functions. It is especially designed to control standard exterior lighting in automotive applications. In order to use the same hardware, the device can be configured to bulb or LED mode for channel 2 and channel 3. As a result, both load types are optimized in terms of switching and diagnosis behavior.

It is specially designed to drive exterior lamps up to 65W, 27W and 10W and HIDL.

Product Summary

Operating Voltage Power Switch		V_{S}	4.5 28 V
Logic Supply Voltage		V_{DD}	3.0 5.5 V
Supply Voltage for Load Dump Protection		$V_{S(LD)}$	40 V
Maximum Stand-By Current at 25 °C		$I_{S(STB)}$	4.5 µA
Typical On-State Resistance at $T_{\rm j}$ = 25 °C	channel 0, 1 channel 2, 3	$R_{\mathrm{DS}(\mathrm{ON},\mathrm{typ})}$	$3.5~\text{m}\Omega$ 11 m Ω
Maximum On-State Resistance at $T_{\rm j}$ = 150 °C	channel 0, 1 channel 2, 3	$R_{\mathrm{DS}(\mathrm{ON},\mathrm{max})}$	9 m Ω 28 m Ω
SPI Access Frequency		$f_{\sf SCLK(max)}$	5 MHz

Туре	Package	Marking
SPOC - BTS5461SF	PG-DSO-36-43	BTS5461SF

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Overview

Configuration and status diagnosis are done via SPI. The SPI is daisy chain capable. The device provides a current sense signal per channel that is multiplexed to the diagnosis pin IS. It can be enabled and disabled via SPI commands. An over load and over temperature flag is provided in the SPI diagnosis word. A multiplexed switch bypass monitor provides short-circuit to $V_{\rm S}$ diagnosis. In OFF state a current source can be switched to the output of one selected channel in order to detect an open load.

The SPOC - BTS5461SF provides a fail-safe feature via limp home input pin.

The power transistors are built by N-channel vertical power MOSFETs with charge pumps.

Protective Functions

- · Reverse battery protection with external components
- ReversaveTM Reverse battery protection by self turn on of all channels
- · Short circuit protection
- Over load protection
- Thermal shutdown with latch and dynamic temperature sensor
- · Over current tripping
- Over voltage protection
- Loss of ground protection
- Electrostatic discharge protection (ESD)

Diagnostic Functions

- Multiplexed proportional load current sense signal (IS)
- Enable function for current sense signal configurable via SPI
- High accuracy of current sense signal at wide load current range
- Current sense ratio ($k_{\rm ILIS}$) configurable for LEDs or bulbs for channel 2 and 3
- · Very fast diagnosis in LED mode
- · Feedback on over temperature and over load via SPI
- Multiplexed switch bypass monitor provides short circuit to $V_{\rm S}$ detection
- Integrated, in two steps programmable current source for open load in OFF-state detection

Application Specific Functions

Fail-safe activation via LHI pin

Applications

- High-side power switch for 12 V grounded loads in automotive applications
- Especially designed for standard exterior lighting like high beam, low beam, indicator, parking light and equivalent LEDs
- Load type configuration via SPI (bulbs or LEDs) for optimized load control
- · Replaces electromechanical relays, fuses and discrete circuits



Block Diagram

2 Block Diagram

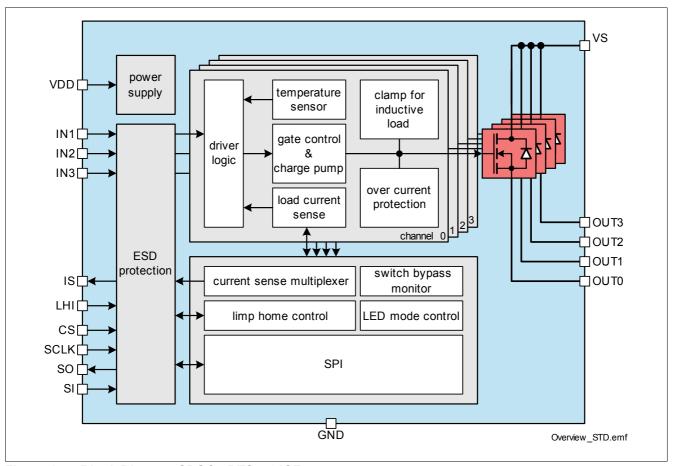


Figure 1 Block Diagram SPOC - BTS5461SF



Block Diagram

2.1 Terms

Figure 2 shows all terms used in this data sheet.

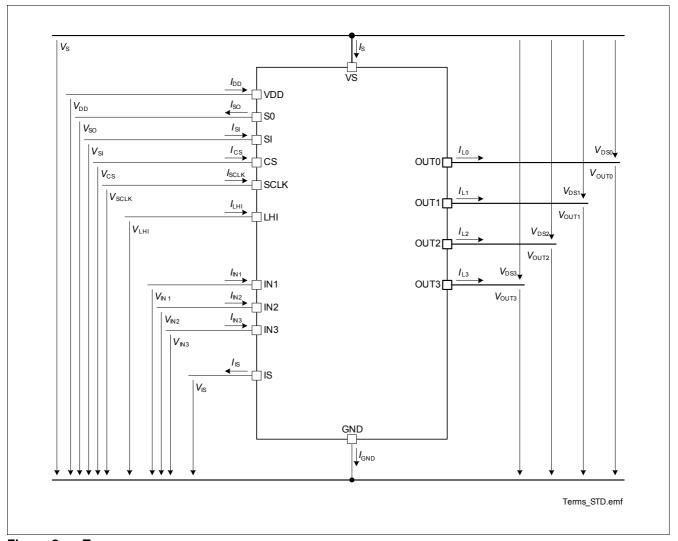


Figure 2 Terms

In all tables of electrical characteristics is valid: Channel related symbols without channel number are valid for each channel separately (e.g. $V_{\rm DS}$ specification is valid for $V_{\rm DS0}$... $V_{\rm DS3}$).

All SPI register bits are marked as follows: ADDR.PARAMETER (e.g. HWCR.CL). In SPI register description, the values in bold letters (e.g. 0) are default values.



Pin Configuration

3 Pin Configuration

3.1 Pin Assignment SPOC - BTS5461SF

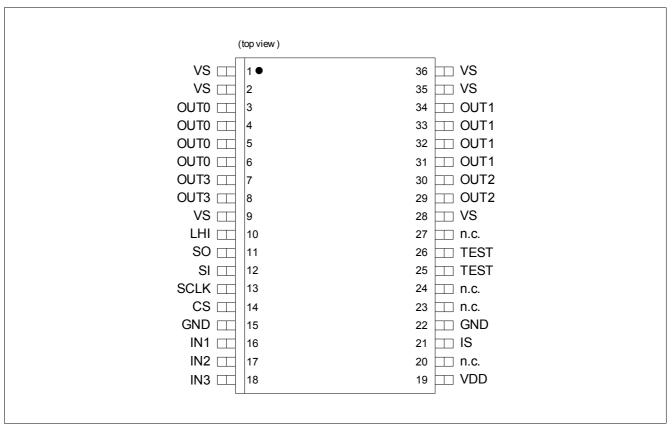


Figure 3 Pin Configuration PG-DSO-36-43



Pin Configuration

3.2 Pin Definitions and Functions

Pin	Symbol	I/O	Function
Power Supply Pins			
1, 2, 9, 28, 35, 36 ¹⁾	VS	_	Positive power supply for high-side power switch
19	VDD	_	Logic supply (5 V)
15, 22	GND	_	Ground connection
Parallel Input Pins (int	tegrated pull-	down	, leave unused pins unconnected)
16	IN1	I	Input signal of channel 1 (high active)
17	IN2	I	Input signal of channel 2 (high active)
18	IN3	I	Input signal of channel 3 (high active)
Power Output Pins		•	
3, 4, 5, 6 ²⁾	OUT0	0	Protected high-side power output of channel 0
31, 32, 33, 34 ²⁾	OUT1	0	Protected high-side power output of channel 1
29, 30 ²⁾	OUT2	0	Protected high-side power output of channel 2
7, 8 ²⁾	OUT3	0	Protected high-side power output of channel 3
SPI & Diagnosis Pins		•	
14	CS	I	Chip select of SPI interface (low active); Integrated pull up
13	SCLK	I	Serial clock of SPI interface
12	SI	I	Serial input of SPI interface (high active)
11	SO	0	Serial output of SPI interface
21	IS	0	Current sense output signal
Limp Home Pin (integ	rated pull-do	wn, pı	ull-down resistor recommended)
10	LHI	I	Limp home activation signal (high active)
Not connected Pins	•	•	
20, 23, 24, 27	n.c.	_	not connected, internally not bonded
25, 26	TEST	_	Test pins, internally bonded and pulled down, do not connect

¹⁾ All $V_{\rm S}$ pins have to be connected.

²⁾ All outputs pins of each channel have to be connected.



Electrical Characteristics

4 Electrical Characteristics

4.1 Absolute Maximum Ratings

Absolute Maximum Ratings 1)

 $T_{\rm j}$ = -40 to +150 °C; all voltages with respect to ground (unless otherwise specified)

Pos.	Parameter	Symbol	Limi	it Values	Unit	Conditions
			min.	max.		
Supply	y Voltage		•	-		
4.1.1	Power supply voltage	V_{S}	-0.3	28	V	_
4.1.2	Logic supply voltage	V_{DD}	-0.3	5.5	V	_
4.1.3	Reverse polarity voltage according Figure 26	-V _{bat(rev)}	_	16	V	T_{jStart} = 25 °C $t \le 2 \text{ min.}^{2}$
4.1.4	Supply voltage for short circuit protection (single pulse)	$V_{\mathrm{S(SC)}}$			V	$R_{\text{ECU}} = 20 \text{ m}\Omega$ $l = 0 \text{ or } 5 \text{ m}^{3)}$
	channel 0, 1		0	24		R_{Cable} = 6 m Ω /m L_{Cable} = 1 μ H/m
	channel 2, 3		0	24		R_{Cable} = 16 m Ω /m L_{Cable} = 1 μ H/m
4.1.5	Supply voltage for load dump protection with connected loads	$V_{\mathrm{S(LD)}}$	_	40	V	$R_1 = 2 \Omega^{4}$ t = 400 ms
4.1.6	Current through ground pin	I_{GND}	_	25	mA	<i>t</i> ≤ 2 min.
4.1.7	Current through VDD pin	I_{DD}	-25	12	mA	<i>t</i> ≤ 2 min.
Power	Stages			-	•	
4.1.8	Load current	I_{L}	_5)	$I_{L(trip)}^{6)}$	Α	
4.1.9	Maximum energy dissipation	E_{AS}			mJ	7)
	single pulse					$T_{\rm j(0)}$ = 150 °C
	channel 0, 1		_	180		$I_{L(0)} = 5 \text{ A}$
	channel 2, 3		_	45		$I_{L(0)} = 2 \text{ A}$
	osis Pin	T.				
4.1.10	Current through sense pin IS	I_{IS}	-8	8	mA	<i>t</i> ≤ 2 min.
Input I	Pins	T.				
4.1.11	Voltage at input pins	V_{IN}	-0.3	5.5	V	_
4.1.12	Current through input pins	I_{IN}	-0.75	0.75	mA	_
			-2.0	2.0		<i>t</i> ≤ 2 min.
SPI Pi	·····		<u> </u>		1	<u> </u>
4.1.13		V_{CS}	-0.3	$V_{\rm DD}$ + 0.3		_
4.1.14	3 1 1	I_{CS}	-2.0	2.0	mA	<i>t</i> ≤ 2 min.
4.1.15		V_{SI}	-0.3	$V_{\rm DD}$ + 0.3	V	_
4.1.16		I_{SI}	-2.0	2.0	mA	<i>t</i> ≤ 2 min.
4.1.17		V_{SCLK}	-0.3	$V_{\rm DD}$ + 0.3		_
4.1.18		I_{SCLK}	-2.0	2.0	mA	<i>t</i> ≤ 2 min.
4.1.19	Voltage at serial output pin	V_{SO}	-0.3	$V_{\rm DD}$ + 0.3	V	_



Electrical Characteristics

Absolute Maximum Ratings (cont'd)1)

 $T_{\rm j}$ = -40 to +150 °C; all voltages with respect to ground (unless otherwise specified)

Pos.	Parameter	Symbol	Lim	it Values	Unit	Conditions
			min.	max.		
4.1.20	Current through serial output pin	I_{SO}	-2.0	2.0	mA	<i>t</i> ≤ 2 min.
Limp H	Home Pin				'	
4.1.21	Voltage at limp home input pin	V_{LHI}	-0.3	5.5	V	_
4.1.22	Current through limp home input pin	I_{LHI}	-0.75	0.75	mA	_
			-2.0	2.0		<i>t</i> ≤ 2 min.
Tempe	eratures					
4.1.23	Junction temperature	T_{i}	-40	150	°C	_
4.1.24	Dynamic temperature increase while switching	$\Delta T_{\rm i}$	_	60	K	_
4.1.25	Storage temperature	$T_{\rm stg}$	-55	150	°C	_
ESD S	usceptibility		1			I
4.1.26	ESD susceptibility HBM	V_{ESD}			kV	HBM ⁸⁾
	OUT pins vs. VS		-4	4		_
	other pins incl. OUT vs. GND)	-2	2		_

- 1) Not subject to production test, specified by design.
- 2) Device is mounted on an FR4 2s2p board according to Jedec JESD51-2,-5,-7 at natural convection; The product (chip+package) was simulated on a 76.4 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70 μm Cu, 2 x 35 μm Cu). Where applicable, a thermal via array under the package contacted the first inner copper layer.
- 3) In accordance to AEC Q100-012 and AEC Q101-006.
- 4) $R_{\rm l}$ is the internal resistance of the load dump pulse generator.
- 5) No protection mechanism available. Inverse current needs to be limited by external circuitry to prevent overheating.
- 6) Over current protection is a protection feature. Operation in over current protection is considered as "outside" normal operating range. Protection features are not designed for continuous repetitive operation.
- 7) Pulse shape represents inductive switch off: $I_{D(t)} = I_{D}(0) \times (1 t / t_{pulse})$; $0 < t < t_{pulse}$
- 8) ESD resistivity, HBM according to ANSI/ESDA/JEDEC JS-001-2010

Note: Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.



Electrical Characteristics

4.2 Thermal Resistance

Note: This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, go to www.jedec.org.

Pos.	Parameter	Symbol	1	Limit Val	ues	Unit	Conditions	
			Min.	Тур.	Max.			
4.2.1	Junction to Soldering Point 1)	R_{thJSP}	_	-	20	K/W	measured to pin 1, 2, 9, 28, 35, 36	
4.2.2	Junction to Ambient 1)	R_{thJA}	_	35	_	K/W	2)	

¹⁾ Not subject to production test, specified by design.

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²⁾ Specified R_{thJA} values is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board; The product (chip+package) was simulated on a 76.4 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70 μm Cu, 2 x 35 μm Cu). Where applicable, a thermal via array under the package contacted the first inner copper layer.



Power Supply

5 Power Supply

The SPOC - BTS5461SF is supplied by two supply voltages $V_{\rm S}$ and $V_{\rm DD}$. The $V_{\rm S}$ supply line is used by the power switches. The $V_{\rm DD}$ supply line is used by the SPI related circuitry and for driving the SO line. A capacitor between pins VDD and GND is recommended as shown in **Figure 26**.

There is a power-on reset function implemented for the $V_{\rm DD}$ logic power supply. After start-up of the logic power supply, all SPI registers are reset to their default values. The SPI interface including daisy chain function is active as soon as $V_{\rm DD}$ is provided in the specified range independent of $V_{\rm S}$. First SPI data are the output register values with TER = 1.

Specified parameters are valid for the supply voltage range according $V_{\rm S(nor)}$ or otherwise specified. For the extended supply voltage range according $V_{\rm S(ext)}$ device functionality (switching, diagnosis and protection functions) are still given, parameter deviations are possible.

5.1 Power Supply Modes

The following table shows all possible power supply modes for $V_{\rm S},\,V_{\rm DD}$ and the pin LHI.

Power Supply Modes	Off	Off	SPI on	Reset	Off	On via INx	Limp Home mode without SPI	Normal operation	Limp Home mode with SPI 1)
$\overline{V_{S}}$	0 V	0 V	0 V	0 V	13.5 V	13.5 V	13.5 V	13.5 V	13.5 V
$\overline{V_{DD}}$	0 V	0 V	5 V	5 V	0 V	0 V	0 V	5 V	5 V
LHI	0 V	5 V	0 V	5 V	0 V	0 V	5 V	0 V	5 V
Power stage, protection	_	_	_	_	_	√ ²⁾	√ ²⁾	✓	√ ²⁾
Limp home	_	_	_	_	_	_	✓	_	✓
SPI (logic)	_	_	✓	✓	reset	reset	reset	✓	reset ³⁾
Stand-by current	_	_	_	_	✓	√ ⁴⁾	_	√ ⁵⁾	_
Idle current	_	_	_	_	-	_	_	√ ⁶⁾	_
Diagnosis	_	_	-	-	_	_	_	✓	√ ⁷⁾

- 1) SPI read only
- 2) Channel 1, 2 and/or 3 activated according to the state of INx
- 3) SPI reset only with applied $V_{\rm S}$ voltage
- 4) When INx = low
- 5) When DCR.MUX = 111_b and INx = low
- 6) When all channels are in OFF-state and DCR.MUX \neq 111_b
- 7) Current sense disabled in limp home mode

5.1.1 Stand-by Mode and Device Wake-up Mechanisms

Stand-by mode is entered as soon as the current sense multiplexer (DCR.MUX) is in default (stand-by) position and all input pins are not set. All error latches are cleared automatically in stand-by mode. As soon as stand-by mode is entered, register HWCR.STB is set. To wake-up the device, the current sense multiplexer (DCR.MUX) is programmed different to default (stand-by) position . The power-on wake up time $t_{WU(PO)}$ has to be considered.

Idle mode parameters are valid, when all channels are switched off, but the current sense multiplexer is not in default position, and $V_{\rm DD}$ supply is available.

Note: A transition from operation to stand-by mode does not reset the SPI registers. So, if $V_{\rm DD}$ is present and SPI is programmed, a changing to ${\tt MUX}$ = 111 $_{\tt b}$ does not reset the SPI registers. An activation of the channels via the input pin INx will wake up the device with the former SPI register settings.



Power Supply

Activating one of the outputs via the input pins (INx = high) will wake-up the device out of stand-by mode. The power stages are working without VDD supply according to the table above. The output turn-on times will be extended by the stand-by channel wake up time $t_{\text{WU(STCH)}}$ as long as no other channel is active. If one channel is active already before channel turn-on times t_{on} (6.5.12) can be considered.

Note: In the operation with V_{DD} = 0 V and INx = high a switching off of all input signals will turn the device in stand-by mode. In stand-by mode the error latches are cleared.

Limp home (LHI = high) applied for a time longer than $t_{\rm LH(ac)}$ will wake-up the device out of stand-by mode after the power-on wake up time $t_{\rm WU(PO)}$ and it is working without VDD supply. Channels 1, 2 and 3 can be activated via the input pins INx. The error latches can be cleared by a low-high transition at the according input pin.

5.2 Reset

There are several reset trigger implemented in the device. They reset the SPI registers including the over temperature latches to their default values. The power stages will switch off, if they are activated via the SPI register <code>OUTL.n.</code> If the power stages are activated via the parallel input pins they are not affected by the reset signals. The ERR-flags are cleared by those reset triggers. The over temperature protection and latches are functional after a reset trigger.

Note: During a reset only the channels 1, 2 and 3 can be activated via the according input pins. The input assigned mode is not available during a reset.

The first SPI transmission after any kind of reset contains at pin SO the read information from the standard diagnosis, the transmission error bit TER is set.

Power-On Reset

The power-on reset is released, when $V_{\rm DD}$ voltage level is higher than $V_{\rm DD(PO)}$. The SPI interface can be accessed after wake up time $t_{\rm WU(PO)}$.

Reset Command

There is a reset command available to reset all register bits of the register bank and the diagnosis registers. As soon as $\mathtt{HWCR.RST} = 1_\mathtt{b}$, a reset is triggered equivalent to power-on reset. The SPI interface can be accessed after transfer delay time $t_{\mathsf{CS(td)}}$.

Limp Home Mode

The limp home mode will be activated as soon as the pin LHI is set to high for a time longer than $t_{\rm LH(ac)}$. The SPI write-registers are reset with applied $V_{\rm S}$ voltage. The outputs OUT1 to OUT3 can be activated via the input pins also during activated limp home mode. The error latches can be cleared by a low-high transition at the according input pin. For application example see **Figure 26**. The SPI interface is operating normally, so the limp home register bit LHI as well as the error flags can be read, but any write command will be ignored.

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Power Supply

Electrical Characteristics 5.3

Electrical Characteristics Power Supply

Unless otherwise specified: $V_{\rm S}$ = 8 V to 17 V, $V_{\rm DD}$ = 3.0 V to 5.5 V, $T_{\rm j}$ = -40 °C to +150 °C typical values: $V_{\rm S}$ = 13.5 V, $V_{\rm DD}$ = 4.3 V, $T_{\rm j}$ = 25 °C

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions
			min.	typ.	max.		
5.3.1	Supply voltage range for normal operation power switch	$V_{S(nor)}$	8	_	17	V	_
5.3.2	Extended supply voltage range for operation power switch	$V_{S(ext)}$	4.5	_	281)	V	Parameter deviations possible
5.3.3	Stand-by current for whole device with loads	$I_{S(STB)}$			4.5 28	μΑ	$V_{\rm DD}$ = 0 V $V_{\rm LHI}$ = 0 V ¹⁾ $T_{\rm j}$ = 25 °C ¹⁾ $T_{\rm j}$ ≤ 85 °C
5.3.4	Idle current for whole device with loads, all channels off	$I_{\mathrm{S(idle)}}$	_	15	_	mA	$V_{\rm DD}$ = 5 V DCR.MUX = 110
5.3.5	Logic supply voltage	V_{DD}	3.0	_	5.5	V	_
5.3.6	Logic supply current	I_{DD}	- -	110 280		μΑ	$\begin{split} V_{\mathrm{CS}} &= V_{\mathrm{LHI}} = 0 \; \mathrm{V} \\ R_{\mathrm{IS}} &= 2.7 \; \mathrm{k}\Omega \\ V_{\mathrm{IS}} &= 0 \; \mathrm{V} \\ f_{\mathrm{SCLK}} &= 0 \; \mathrm{Hz} \\ f_{\mathrm{SCLK}} &= 5 \; \mathrm{MHz} \end{split}$
5.3.7	Logic stand-by current	$I_{\rm DD(STB)}$	_	25	_	μΑ	$\begin{split} V_{\mathrm{CS}} &= V_{\mathrm{DD}} \\ f_{\mathrm{SCLK}} &= 0 \; \mathrm{Hz} \\ \mathrm{Chip \; in \; Stand-by} \end{split}$
5.3.8	Operating current for whole device active	I_{GND}	_	10	25	mA	$f_{\rm SCLK}$ = 0 Hz
LHI In	put Characteristics	•					
5.3.9	L-input level at LHI pin	$V_{\mathrm{LHI(L)}}$	0	_	8.0	V	_
5.3.10	H-input level at LHI pin	$V_{\mathrm{LHI(H)}}$	1.8	_	5.5	V	_
5.3.11	L-input current through LHI pin	$I_{LHI(L)}$	3	12	80	μΑ	$^{1)} V_{LHI} = 0.6 \text{ V}$
5.3.12	H-input current through LHI pin	$I_{\mathrm{LHI(H)}}$	10	40	80	μΑ	V_{LHI} = 5 V
Reset							
5.3.13	Power-On reset threshold voltage	$V_{\rm DD(PO)}$	1	_	2.4	V	_
5.3.14	Power-On wake up time	$t_{\rm WU(PO)}$	_		200	μs	1)
5.3.15	Stand-by channel wake up time	$t_{\rm WU(STCH)}$	-	_	200	μs	1)
5.3.16	Limp home acknowledgement time	$t_{\rm LH(ac)}$	5	_	200	μs	1)

¹⁾ Not subject to production test, specified by design.

Note: Characteristics show the deviation of parameter at the given supply voltage and junction temperature.



6 Power Stages

The high-side power stages are built by N-channel vertical power MOSFETs (DMOS) with charge pumps. There are four channels implemented in the device. Channels can be switched on via an input pin (please refer to Section 6.2) or via SPI register OUTL.

6.1 Output ON-State Resistance

The on-state resistance $R_{\rm DS(ON)}$ depends on the supply voltage $V_{\rm S}$ as well as on the junction temperature $T_{\rm j}$. Figure 4 shows those dependencies. The behavior in reverse polarity mode is described in Section 7.5.

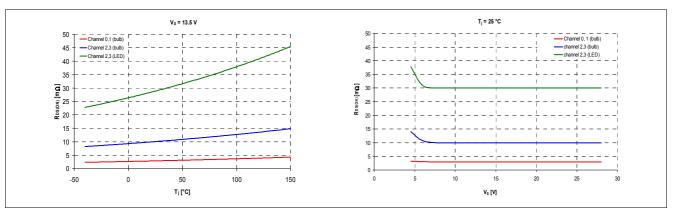


Figure 4 Typical On-State Resistance

6.2 Input Circuit

The outputs of the SPOC - BTS5461SF can be activated either via the SPI register <code>OUTL.OUTh</code> or via the dedicated input pins. There are two different ways to use the input pins, the direct drive mode and the assigned drive mode. The default setting is the direct drive mode. To activate the assigned drive mode the register bit <code>ICR.INCG</code> needs to be set.

Additionally, there are two ways of using the input pins in combination with the OUTL register by programming the ICR.COL parameter.

- ICR.COL = 0_b: A channel is switched on either by the according OUTL register bit or the input pin.
- ICR.COL = 1_b: A channel is switched on by the according OUTL register bit only, when the input pin is high. In this configuration, a PWM signal can be applied to the input pin and the channel is activated by the SPI register OUTL.

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Figure 5 shows the complete input switch matrix.

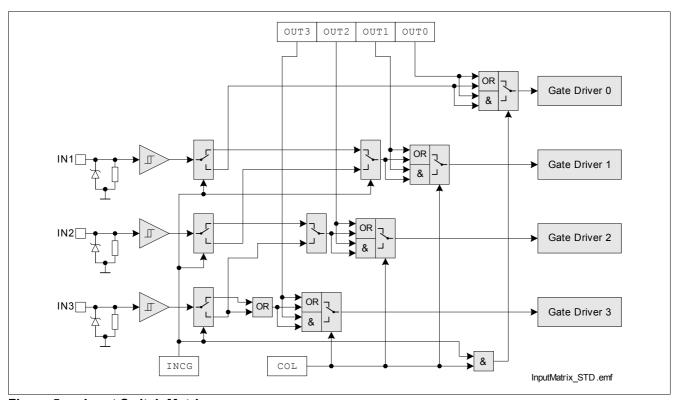


Figure 5 Input Switch Matrix

The current sink to ground ensures that the input signal is low in case of an open input pin. The zener diode protects the input circuit against ESD pulses.

6.2.1 Input Direct Drive

This mode is the default after the device's wake up and reset. The input pins activate the channels during normal operation (with default setting of bit ICR.INCG), stand-by mode and limp home mode. Channel 0 can be activated only via the SPI-bit OUTL.OUTO in direct drive mode. The inputs are linked directly to the channels according to:

Table 1 Direct Drive Mode

Input Pin	Assigned channel , if ICR. INCG = 0_b				
IN1	Channel 1				
IN2	Channel 2				
IN3	Channel 3				

6.2.2 Input Assigned Drive

To activate the assigned drive function the register bit ICR. INCG needs to be set. In this mode all output channels can be activated via the input pins. Channel 2 and 3 are assigned to only one input pin. The following mapping is used:



Table 2 Assigned Drive Mode

Input Pin	Assigned channel, if ICR.INCG = 1 _b
IN1	Channel 0
IN2	Channel 1
IN3	Channel 2, channel 3

6.3 Power Stage Output

The power stages are built to be used in high side configuration (Figure 6).

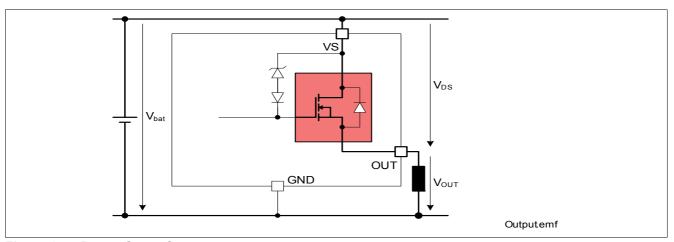


Figure 6 Power Stage Output

The power DMOS switches with a dedicated slope, which is optimized in terms of EMC emission. Defined slew rates and edge shaping allow lowest EMC emissions during PWM operation at low switching losses.

6.3.1 Bulb and LED mode

Channel 2 and channel 3 can be configured in bulb and LED mode via the SPI registers <code>hwcr.ledn</code>. During LED mode following parameters are changed for an optimized functionality with LED loads: On-state resistance $R_{\rm DS(ON)}$, switching timings ($t_{\rm delay(ON)}$, $t_{\rm delay(OFF)}$, $t_{\rm ON}$, $t_{\rm OFF}$), slew rates ${\rm d}V/{\rm d}t_{\rm ON}$ and ${\rm d}V/{\rm d}t_{\rm OFF}$, current protections $I_{\rm L(trip)}$ and current sense ratio $k_{\rm ILIS}$.



6.3.2 Switching Resistive Loads

When switching resistive loads the following switching times and slew rates can be considered.

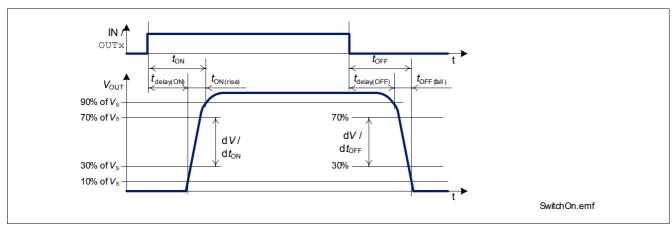


Figure 7 Switching a Load (resistive)

6.3.3 Switching Inductive Loads

When switching off inductive loads with high-side switches, the voltage $V_{\rm OUT}$ drops below ground potential, because the inductance intends to continue driving the current. To prevent the destruction of the device due to high voltages, there is a voltage clamp mechanism implemented, which limits that negative output voltage to a certain level ($V_{\rm DS(CL)}$ (6.5.2)). See **Figure 6** for details. The device provides SmartClamp functionality. To increase the energy capability, the clamp voltage $V_{\rm DS(CL)}$ increases with the junction temperature $T_{\rm j}$ and load current $I_{\rm L}$. Please refer also to **Section 7.6**. The maximum allowed load inductance is limited.

6.3.4 Switching high inrush loads

When switching loads with high inrush currents like e.g. high capacitive loads, it has to be ensured that in normal operating range the maximum load current is below the current trip level of the device. If the current trip level is touched, the device would operate under fault conditions that are considered as outside normal operating range. In this case absolute maximum ratings are exceeded (I_{Ltrip} (4.1.8)). Please refer to Section 4 and Section 7 for further information.

6.4 Inverse Current Behavior

During inverse currents ($V_{\text{OUT}} > V_{\text{S}}$) the affected channel stays in ON- or in OFF-state. Furthermore, during applied inverse currents no ERR-flag is set.

The functionality of unaffected channels is not influenced by inverse currents applied to other channels (except effects due to junction temperature increase). Influences on the diagnostic function of unaffected channels are possible only for the current sense ratio, please refer to $\Delta k_{\text{ILIS}(IC)}$ (8.5.3).

Note: No protection mechanism like temperature protection or current protection is active during applied inverse currents. Inverse currents cause power losses inside the DMOS, which increase the overall device temperature, which could lead to a switch off of the unaffected channels due to over temperature.

Data Sheet 18 Rev. 1.0, 2011-11-17



6.5 **Electrical Characteristics**

Electrical Characteristics Power Stages

Pos.	Parameter	Symbol	Limit Values		Limit Values Unit		Test Conditions
			min.	typ.	max.		
Outp	ut Characteristics		_I	_I		1	L
6.5.1	On-state resistance	$R_{DS(ON)}$				$m\Omega$	
	channel 0, 1	==(=::)					<i>I</i> _L = 7.5 A
	·		_	3.5	_		$T_{\rm j} = 25 {\rm ^{\circ}C}$
			_	7	9		$T_{\rm j} = 150 ^{\circ}{\rm C}$
	channel 2, 3						HWCR.LEDn = 0
							$I_{\rm L}$ = 2.6 A
			-	11	-		¹⁾ $T_{\rm j}$ = 25 °C
			_	22	28		$T_{\rm j}$ = 150 °C
							HWCR.LEDn = 1
				20			$I_{\rm L} = 0.6 {\rm A}$
			_	39 78	100		$T_{\rm j} = 25 ^{\circ}{\rm C}$
0.50	Outrat dame	I/	_	10	100	V	T _j = 150 °C
6.5.2	Output clamp	$V_{DS(CL)}$	00		- 4	V	T. 05.00
	channel 0, 1		32	_	54		$T_{\rm j}$ = 25 °C $I_{\rm L}$ = 20 mA
			40		55		$T_{\rm L} = 20 \text{MA}$ $T_{\rm i} = 150 ^{\circ}\text{C}$
			40	_	33		$I_{L} = 6 \text{ A}$
	channel 2, 3		32	_	54		T _i = 25 °C
	, ,						$I_{\rm L}^{\rm J}$ = 20 mA
			40	_	55		$_{\rm j}^{1)} T_{\rm j} = 150 ^{\circ}{\rm C}$
							I _L = 2 A
6.5.3	Output leakage current per channel in	$I_{L(OFFSTB)}$				μA	OUTL.OUTn = 0
	stand-by						DCR.MUX = 111
	channel 0, 1		-	-	2		$T_{\rm j}$ = 25 °C
			_	_	10		$\binom{1)^{J}}{T_{j}} = 85 ^{\circ}\text{C}$
			_	_	50		$T_{\rm j}^{(1)} = 105 ^{\circ}{\rm C}$
	channel 2, 3		_	_	1		$T_{\rm j}$ = 25 °C
			_	_	4		$T_{\rm j} = 85 ^{\circ}{\rm C}$
0.5.4		7	_	_	20		¹⁾ $T_{\rm j}$ = 105 °C
6.5.4	Output leakage current per channel in idle	$I_{L(OFFidle)}$				μA	OUTL.OUTN = 0
	mode				00		DCR.MUX ≠ 111
	channel 0, 1		-	_	60		$^{(1)}T_{\rm j} = 85 ^{\circ}{\rm C}$
				_	80 530		$T_{\rm j}^{(1)} = 105 ^{\circ}{\rm C}$
	ahanii al O. O			_			$T_{\rm j}$ = 150 °C
	channel 2, 3			_	45 50		¹⁾ $T_{\rm j}$ = 85 °C ¹⁾ $T_{\rm j}$ = 105 °C
				_	230		$T_{\rm j} = 100 ^{\circ} \text{C}$
					200		1 100 U



Electrical Characteristics Power Stages (cont'd)

Pos.	Parameter	Symbol	ol Limit Values		lues Unit		Test Conditions
			min.	typ.	max.		
6.5.5	Inverse current capability per channel	$-I_{L(IC)}$				Α	1) No influences on
	channel 0, 1		6	_	_		switching functionality of
	channel 2, 3		2	_	_		unaffected channels, $k_{\rm ILIS}$ influence according $\Delta k_{\rm ILIS(IC)}$ (8.5.3)
Input	Characteristics		1	1	1	1	12.5(13)
6.5.6	L-input level	$V_{IN(L)}$	0	_	0.8	V	-
6.5.7	H-input level	$V_{\rm IN(H)}$	1.8	_	5.5	V	_
6.5.8	L-input current	$I_{IN(L)}$	3	12	80	μΑ	$^{1)} V_{IN} = 0.6 \text{ V}$
6.5.9	H-input current	$I_{IN(H)}$	10	40	80	μΑ	V _{IN} = 5 V



Electrical Characteristics Power Stages (cont'd)

Pos.	Parameter	Symbol	Lin	Limit Values		Unit	Test Conditions	
			min. typ.		max.			
Timin	gs				•			
6.5.10	Turn-ON delay to 10% $V_{ m S}$	$t_{\rm delay(ON)}$				μs	$^{1)} V_{\rm S}$ = 13.5 V	
	channel 0, 1		_	35	_		_	
	channel 2, 3		_	25	_		HWCR.LEDn = 0	
			_	8	_		HWCR.LEDn = 1	
6.5.11	Turn-OFF delay to 90% $V_{ m S}$	$t_{\rm delay(OFF)}$				μs	$^{1)}$ $V_{\rm S}$ = 13.5 V	
	channel 0, 1	, ,	_	55	_		_	
	channel 2, 3		_	30	_		HWCR.LEDn = 0	
			_	10	_		HWCR.LEDn = 1	
6.5.12	Turn-ON time to	$t_{\sf ON}$				μs	V _S = 13.5 V	
	90% $V_{\rm S}$ including turn-ON delay						DCR.MUX ≠111	
	channel 0, 1		_	_	100		$R_{\rm L}$ = 2.2 Ω	
	channel 2, 3		_	_	100		HWCR.LEDn = 0	
							$R_{\rm L}$ = 6.8 Ω	
			_	_	50		HWCR.LEDn = 1	
							$R_{\rm L}$ = 33 Ω	
6.5.13	Turn-OFF time to	t_{OFF}				μs	$V_{\rm S}$ = 13.5 V	
	10% $V_{ m S}$ including turn-OFF delay				450		D 000	
	channel 0, 1		_	_	150		$R_{\rm L}$ = 2.2 Ω	
	channel 2, 3		_	_	110		HWCR.LEDn = 0 $R_{\rm L}$ = 6.8 Ω	
			_	_	50		$R_L = 0.0 \Omega$ HWCR.LEDn = 1	
							$R_{\rm L}$ = 33 Ω	
6.5.14	Turn-ON rise time from 10% to	$t_{ON(rise)}$				μs	V _S = 13.5 V	
	90% V _S	ON(IISE)				•	DCR.MUX ≠111	
	channel 0, 1		_	_	55		$R_1 = 2.2 \Omega$	
	channel 2, 3		_	_	55		HWCR.LEDn = 0	
							$R_{\rm L}$ = 6.8 Ω	
			_	_	11		HWCR.LEDn = 1	
							$R_{\rm L}$ = 33 Ω	
6.5.15	Turn-OFF fall time from 90% to 10% $V_{\rm S}$	$t_{OFF(fall)}$				μs	V _S = 13.5 V	
	channel 0, 1		_	_	55		R_{L} = 2.2 Ω	
	channel 2, 3		_	_	55		HWCR.LEDn = 0	
							$R_{\rm L}$ = 6.8 Ω	
			-	-	11		HWCR.LEDn = 1	
							$R_{\rm L}$ = 33 Ω	



Electrical Characteristics Power Stages (cont'd)

Pos.	Parameter		Symbol Limit Va			Values Un		Test Conditions
				min.	typ.	max.		
6.5.16	Turn-ON/OFF matching		$ t_{\text{ON}} - t_{\text{OFF}} $				μs	V _S = 13.5 V
		channel 0, 1		_	_	90		$R_{\rm L}$ = 2.2 Ω
		channel 2, 3		_	_	70		HWCR.LEDn = 0 $R_1 = 6.8 \Omega$
				-	_	50		HWCR.LEDn = 1 $R_{\rm L}$ = 33 Ω
6.5.17	Turn-ON slew rate 30% to 70% $V_{\rm S}$		dV/dt_{ON}				V/µs	V _S = 13.5 V
		channel 0, 1		0.2	0.7	2.0		$R_{\rm L}$ = 2.2 Ω
		channel 2, 3		0.2	0.9	2.5		HWCR.LEDn = 0 $R_1 = 6.8 \Omega$
				0.6	2.5	6.0		HWCR.LEDn = 1 $R_{\rm L}$ = 33 Ω
6.5.18	Turn-OFF slew rate 70% to 30% $V_{\rm S}$		$-dV/$ dt_{OFF}				V/µs	V _S = 13.5 V
		channel 0, 1		0.2	0.7	2.0		R_{L} = 2.2 Ω
		channel 2, 3		0.2	0.9	2.5		HWCR.LEDn = 0 $R_L = 6.8 \Omega$
				0.6	2.5	6.0		HWCR.LEDn = 1 $R_{\rm L}$ = 33 Ω

¹⁾ Not subject to production test, specified by design.



7 Protection Functions

The device provides embedded protective functions, which are designed to prevent IC destruction under fault conditions described in this data sheet. Fault conditions are considered as "outside" normal operating range. Protective functions are neither designed for continuous nor for repetitive operation.

7.1 Over Current Protection

The maximum load current $I_{\rm L}$ is switched off in case of exceeding the over current trip level $I_{\rm L(trip)}$ by the device itself. Depending on the total short circuit impedance higher current over shoots may occur. A limited auto-restart function is implemented. The number of restarts is dependent of the $V_{\rm DS}$ voltage. Please refer to following figures for details.

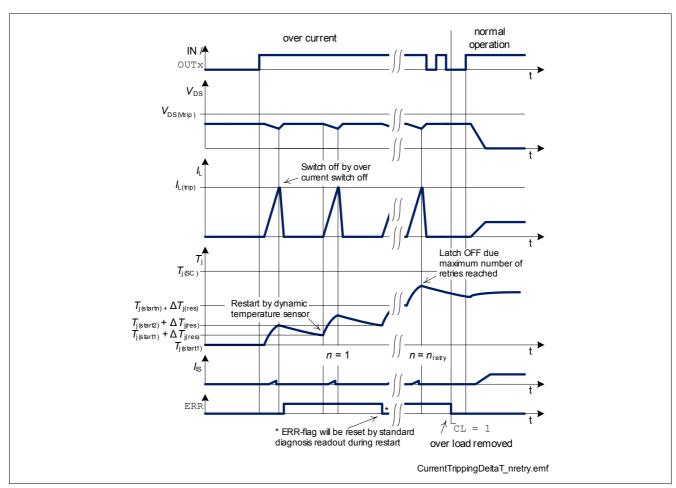


Figure 8 Over current protection with latch due to reaching maximum number of retries n_{retry}



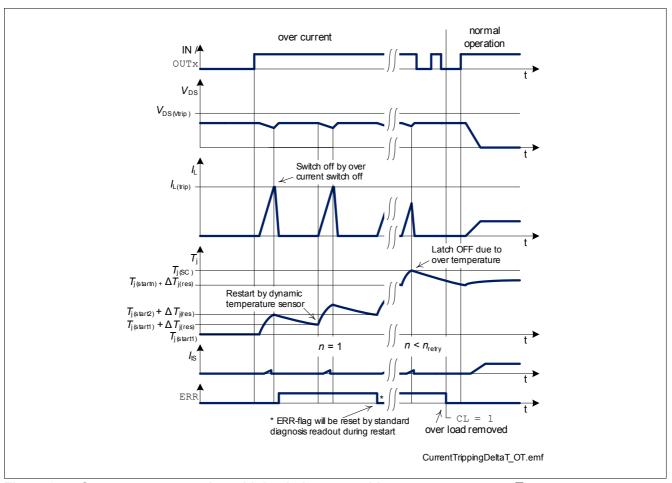


Figure 9 Over current protection with latch due to reaching over temperature $T_{\rm j(SC)}$

The ERR-flag will be set during over current shut down. It can be reset by reading the ERR-flag. If the channel is still in over current shut down, the ERR-flag will be set again. During the automatic restart of the channel the ERR-flag can be cleared by reading the ERR-flag. It will be set again as soon as the over current protection is activated again.

The number of restarts n_{retry} is depending on the V_{DS} voltage according to the following figure and Chapter 7.2.

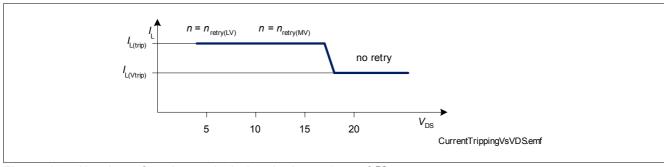


Figure 10 Number of retries and trip levels dependent of $V_{
m DS}$

The retry latch or over temperature latch is cleared by SPI command $\mathtt{HWCR.CL} = 1_{\mathtt{b}}$. If the input pin or the bit in the SPI register \mathtt{OUTL} is still set, the channel will be turned on immediately after the command $\mathtt{HWCR.CL} = 1_{\mathtt{b}}$. To prevent degradation of the device it is recommended to wait $t_{\mathsf{reset(CL)}}$ (7.9.9) until resetting the latch.



7.2 Over Current Protection at high V_{DS}

The SPOC - BTS5461SF provides an over current protection for $V_{\rm DS} > V_{\rm DS(Vtrip)}$ (7.9.5). For $V_{\rm DS} > V_{\rm DS(Vtrip)}$ and $I_{\rm L} > I_{\rm L(Vtrip)}$ during turn on the channel switches off and latches immediately. For details please refer to parameter $I_{\rm L(VTRIP)}$ (7.9.4).

The current trip level $I_{\text{L(Vtrip)}}$ is below the current trip level $I_{\text{L(trip)}}$ at V_{DS} = 7V. The ratio between $I_{\text{L(trip)}}$ and $I_{\text{L(Vtrip)}}$ is defined by the parameter Δk_{TR} (7.9.6).

The over current latch is cleared by SPI command HWCR.CL = 1_b . If the input pin or the bit in the SPI register OUTL is still set, the channel will be turned on immediately after the command HWCR.CL = 1_b . To prevent degradation of the device it is recommended to wait $t_{reset(CL)}$ (7.9.9) until resetting the latch.

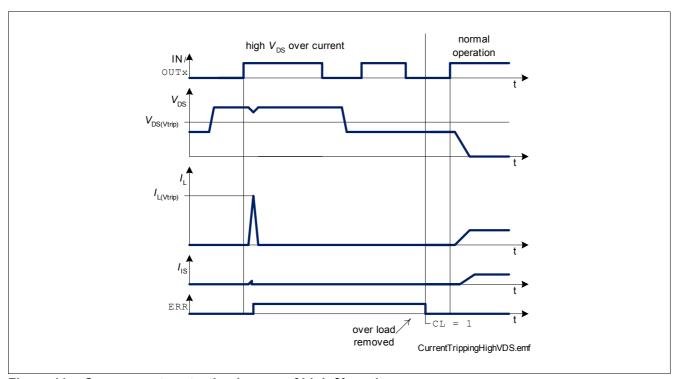


Figure 11 Over current protection in case of high $V_{
m DS}$ voltages

7.3 Over Current Protection for Short Circuit Type 2 Protection

After activation of the channels without over temperature shutdown and after the delay time $t_{\rm delay(trip)}$ (7.9.2) the over current protection threshold $I_{\rm L(trip)}$ is reduced to $I_{\rm L(ltrip)}$. The delay time $t_{\rm delay(trip)}$ is reset by an dynamic temperature sensor or over current shutdown and any IN or OUTL. In case of a short circuit to GND event with $I_{\rm L} > I_{\rm L(ltrip)}$ (7.9.3), which occurs in the on state, the channel is switched off and latched immediately. For more details, please refer to the figure **Figure 12**.

The current trip level $I_{\text{L(Itrip)}}$ is below the current trip level $I_{\text{L(trip)}}$ at V_{DS} = 7V. The ratio between $I_{\text{L(trip)}}$ and $I_{\text{L(Itrip)}}$ is defined by the parameter Δk_{TR} (7.9.6).

The over current latch is cleared by SPI command $HWCR.CL = 1_b$. If the input pin or the bit in the SPI register OUTL is still set, the channel will be turned on immediately after the command $HWCR.CL = 1_b$. To prevent degradation of the device it is recommended to wait $t_{reset(CL)}$ (7.9.9) until resetting the latch.



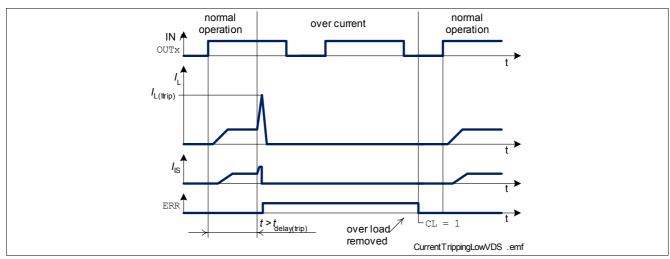


Figure 12 Shut Down by Over Current due to Short Circuit Type 2

7.4 Over Temperature Protection

Each channel has its own temperature sensor. If the temperature at the channel exceeds the thermal shutdown temperature $T_{\rm j(SC)}$, the channel will switch off and latch to prevent destruction (also in case of $V_{\rm DD}$ = 0V). In order to reactivate the channel, the temperature at the output must drop by at least the thermal hysteresis $\Delta T_{\rm j}$ and the over temperature latch must be cleared by SPI command HWCR.CL = $1_{\rm b}$. If the input pin or the bit in the SPI register OUTL is still set, the channel will be turned on immediately after the command HWCR.CL = $1_{\rm b}$.To prevent degradation of the device it is recommended to wait $t_{\rm reset(CL)}$ (7.9.9) until resetting the latch.

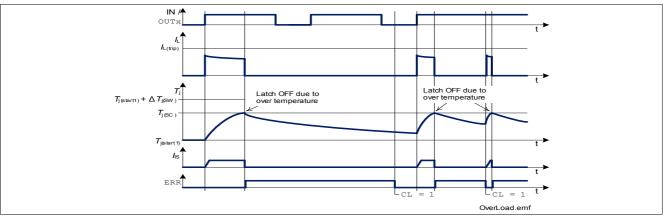


Figure 13 Shut Down by Over Temperature

7.4.1 Dynamic Temperature Sensor Protection

Additionally, each channel has its own dynamic temperature sensor. The dynamic temperature sensor improves short circuit robustness by limiting sudden increases in the junction temperature. The dynamic temperature sensor turns off the channel if its sudden temperature increase exceeds the dynamic temperature sensor threshold $\Delta T_{\rm j(SW)}$. The number of automatic reactivations is limited by $n_{\rm retry}$ (7.9.7). If this number of retries is exceeded the channel turns off and latches. The retry latch is cleared by SPI command HWCR.CL = $1_{\rm b}$. If the input pin or the bit in the SPI register OUTL is still set, the channel will be turned on immediately after the command HWCR.CL = $1_{\rm b}$. To prevent degradation of the device it is recommended to wait $t_{\rm reset(CL)}$ (7.9.9) until resetting the latch. For the condition $n < n_{\rm retry}$ the counter of automatic reactivations will be reset by every low to high transition on the input pin or the bit in SPI register OUTL.

Please refer to Figure 12 for details.



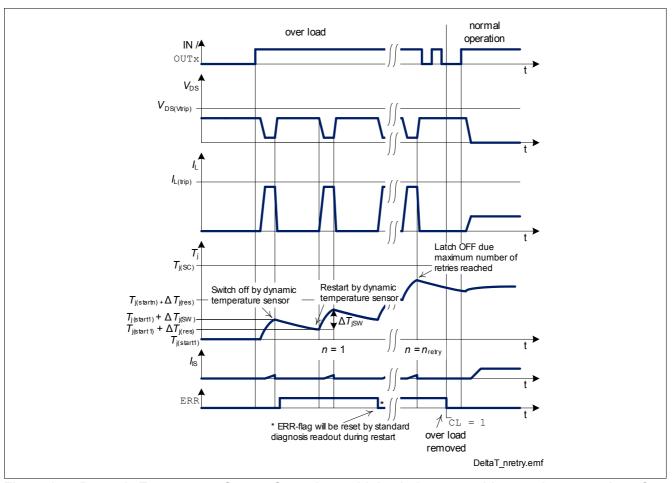


Figure 14 Dynamic Temperature Sensor Operations with latch due to reaching maximum number of retries $n_{\rm retry}$



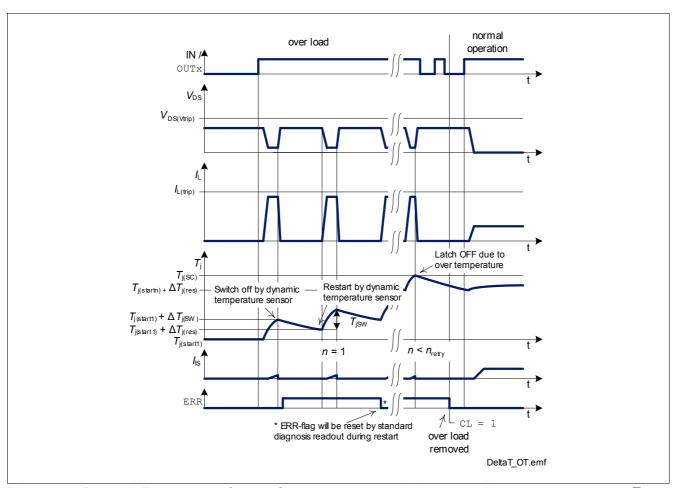


Figure 15 Dynamic Temperature Sensor Operations with latch due to reaching over temperature $T_{\rm i(SC)}$

The ERR-flag will be set during dynamic temperature sensor shut down. It can be reset by reading the ERR-flag. If the channel is still in dynamic temperature sensor shut down, the ERR-flag will be set again. During the automatic restart of the channel the ERR-flag can be cleared by reading the ERR-flag. It will be set again as soon as the dynamic temperature sensor is activated again.

7.5 Reverse Polarity Protection - ReversaveTM

In reverse polarity mode, power dissipation is caused by the reverse ON-state resistance $R_{\rm DS(REV)}$ of each channel as well as each ESD diode of the logic pins. The reverse current through the channels has to be limited by the connected loads. The current through the sense pin IS, the logic power supply pin VDD, the SPI pins, input pins and the limp home input pin has to be limited as well (please refer to the maximum ratings listed on **Page 9**).

For reducing the power loss during reverse polarity ReversaveTM functionality is implemented for all channels. They are turned on to almost forward condition in reverse polarity condition, see parameter $R_{DS(REV)}$.

Note: No protection mechanism like temperature protection or current protection is active during reverse polarity.

7.6 Over Voltage Protection

In the case of supply voltages between $V_{\rm S(SC)\,max}$ and $V_{\rm S(CL)}$ the output transistors are still operational and follow the input or the OUTL register. Parameters are not warranted and lifetime is reduced compared to normal mode.

In addition to the output clamp for inductive loads as described in **Section 6.3**, there is a clamp mechanism available for over voltage protection for the logic and all channels.



7.7 Loss of Ground

In case of complete loss of the device ground connections, but connected load ground, the SPOC - BTS5461SF securely changes to or stays in OFF-state.

7.8 Loss of V_s

In case of loss of $V_{\rm S}$ connection in on-state, all inductances of the loads have to be demagnetized through the ground connection or through an additional path from VS to GND. For example, a suppressor diode is recommended between VS and GND.



7.9 Electrical Characteristics

Electrical Characteristics Protection Functions

Pos.	Parameter	Symbol	Limit Values		ues	Unit	Test Conditions	
			min.	typ. max.				
Over	Load Protection				·			
7.9.1	Load current trip level	$I_{L(trip)}$				Α	$V_{\rm DS}$ < 7 V	
	channel 0, 1		71	_	120		$T_{\rm i}$ = -40 °C	
			_	90	-		$T_{\rm j}$ = -40 °C ¹⁾ $T_{\rm j}$ = 25 °C	
			67	_	100		$T_{\rm j}$ = 150 °C	
	channel 2, 3						HWCR.LEDn = 0	
			29	_	44		$T_{\rm j}$ = -40 °C	
			-	30	_		$T_{\rm j} = 25 ^{\circ}{\rm C}$	
			23	-	39		$T_{\rm j} = 150 ^{\circ}{\rm C}$	
			_		40		HWCR.LEDn = 1	
			7	_ 0.5	12		$T_{\rm j} = -40 ^{\circ}{\rm C}$	
			- 5.5	8.5	11		$T_{\rm j} = 25 ^{\circ}{\rm C}$ $T_{\rm i} = 150 ^{\circ}{\rm C}$	
0,,,,,,,,	Current Protection		5.5		11		I _j - 150 C	
		4	7		1.1	T	1)	
7.9.2	0	t _{delay(trip)}	7	_	14	ms	,	
7.9.3	· aciay(trip)	$I_{L(Itrip)}$				Α		
	channel 0, 1		40	_	78		$T_{\rm j}$ = -40 °C	
			35	_	70		$T_{\rm j}$ = 150 °C	
	channel 2, 3		4-7		0.5		HWCR.LEDn = 0	
			17 15.5	_	35		$T_{\rm j}$ = -40 °C	
			15.5	-	30		$T_{\rm j}$ = 150 °C	
			3.8		0		HWCR.LEDn = 1	
			3.8	_	9		$T_{\rm j}$ = -40 °C $T_{\rm i}$ = 150 °C	
7.9.4	Load current trip level at high $V_{ m DS}$	I	0.0		0	Α	1)	
7.3.4	= 4	$I_{L(Vtrip)}$	40		70	^	T - 40 °C	
	channel 0, 1		40 35		78 70		$T_{\rm j}$ = -40 °C $T_{\rm i}$ = 150 °C	
	channel 2, 3		33		70		ž	
	Charmer 2, 3		17	_	35		HWCR.LEDn = 0 $T_i = -40 ^{\circ}\text{C}$	
			15.5		30		$T_{\rm j} = 150 ^{\circ}{\rm C}$	
			10.0				HWCR.LEDn = 1	
			3.8	_	9		$T_i = -40 ^{\circ}\text{C}$	
			3.8	_	8		$T_{\rm i}$ = 150 °C	
7.9.5	Over current tripping at high $V_{ m DS}$	$V_{\mathrm{DS(Vtrip)}}$	15	_	_	V	1)	
	activation level	บอ(งแb)						
7.9.6	Current trip at V_{DS} = 7 V to current trip at	Δk_{TR}	1.2	1.5	_		1)	
-	$V_{\rm DS}$ = 20 V ratio	711						



Electrical Characteristics Protection Functions (cont'd)

Pos.	Parameter	Symbol	Limit Values			Unit	Test Conditions	
			min.	typ. max.				
Over	Temperature Protection		•	•	•			
7.9.7	Number of automatic retries at over current or dynamic temperature sensor shut down at low $V_{\rm DS}$	n _{retry(LV)}	_	32	_		¹⁾ V _{DS} = 9 V	
7.9.8	Number of automatic retries at over current or dynamic temperature sensor shut down at medium $V_{\rm DS}$	n _{retry(MV)}	_	8	-		¹⁾ V _{DS} = 13 V	
7.9.9	Thermal latch restart time	$t_{ m reset(CL)}$	50	_	_	ms	1)	
7.9.10	Thermal shut down temperature	$T_{\rm j(SC)}$	150	175	195	°C	1)	
7.9.11	Thermal hysteresis of thermal shutdown	$\Delta T_{\rm j}$	_	10	_	K	1)	
7.9.12	Dynamic temperature increase limitation while switching	$\Delta T_{\rm j(SW)}$	_	60	-	K	1)	
7.9.13	Dynamic temperature sensor restart	$\Delta T_{\rm j(res)}$	_	20	_	K	1)	
Rever	se Battery		"	1				
7.9.14	On-state resistance	$R_{\rm DS(REV)}$				$m\Omega$	$^{1)} V_{\rm S} = -13.5 \text{ V}$	
	channel 0, 1		_	4.7 9.5	_ _		I_{L} = -7.5 A T_{j} = 25 °C T_{j} = 150 °C	
	channel 2, 3			14.7 29.5	 - -		$I_{\rm L}$ = -2.6 A $T_{\rm j}$ = 25 °C $T_{\rm i}$ = 150 °C	
Over	Voltage						1 3	
7.9.15	Over voltage protection VS to GND	$V_{\mathrm{S(CL)}}$	40	55	71	V	$I_{\rm GND}$ = 5 mA	
	channel 0, 1		32	_	54		$T_{\rm j}$ = 25 °C $I_{\rm l}$ = 20 mA	
			40	_	55		$T_{\rm L} = 150 ^{\circ}{\rm C}$ $I_{\rm L} = 6 {\rm A}$	
	channel 2, 3		32	_	54		$T_{\rm j}$ = 25 °C $I_{\rm L}$ = 20 mA	
			40	_	55		$T_{\rm j} = 150~{\rm ^{\circ}C}$ $T_{\rm L} = 2~{\rm A}$	

¹⁾ Not subject to production test, specified by design.



8 Diagnosis

For diagnosis purpose, the SPOC - BTS5461SF provides a current sense signal at pin IS and the diagnosis word via SPI. There is a current sense multiplexer implemented that is controlled via SPI. The sense signal can also be disabled by SPI command. A switch bypass monitor allows to detect a short circuit between the output pin and the battery voltage.

In OFF-state a current source is able to be switched on for a selected channel with the DCR.CSOL bit. This allows open load / short circuit detection to V_S in OFF-state. The current value can be configured to a low or a high value by programming the bit ICR.CSL. Please refer to parameter $I_{L(OL)}$ (8.5.15).

Please refer to Figure 16 for details on diagnosis function:

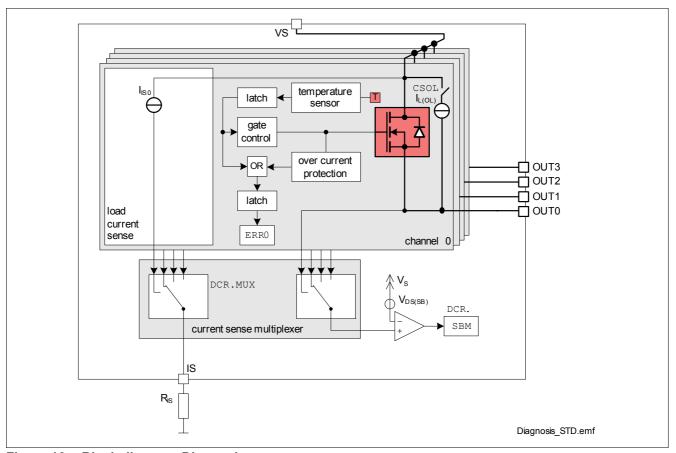


Figure 16 Block diagram: Diagnosis



For diagnosis feedback at different operation modes, please see following table.

Table 3 Operation Modes 1)

Operation Mode	Input Level	Output	Current	Error Flag	SBM
	OUTL.OUTn	Level V_{OUT}	Sense $I_{\rm IS}$	ERRn ²⁾	DCR.SBM
Normal Operation (OFF)	L/0	GND	Z	0	1
Short Circuit to GND	(OFF-state)	GND	Z	0	1
Thermal shut down		Z	Z	0	х
Short Circuit to V_{S}		V_{S}	Z	0	0
Open Load		Z	Z	0	03)
Inverse Current		> V _S	Z	0	04)
Normal Operation (ON)	H/1	~ V _S	$I_{\rm L}/k_{\rm ILIS}$	0	0
Short Circuit to GND	(ON-state)	~ GND	Z	1	1
Dynamic Temperature Sensor shut down		Z	Z	1	х
Over Current shut down		Z	Z	1 ⁵⁾	х
Thermal shut down		Z	Z	1 ⁶⁾	х
Short Circuit to $V_{\mathbb{S}}$		V_{S}	$< I_{L} / k_{ILIS}$	0	0
Open Load		V_{S}	Z	0	0
Inverse Current	1	> V _S	Z	0	0

- 1) L = low level, H = high level, Z = high impedance, potential depends on leakage currents and external circuit x = undefined
- 2) The error flags are latched until they are transmitted in the standard diagnosis word via SPI
- 3) If the current sense multiplexer is set to Channel 0 to 3 and DRC.CSOL bit set
- 4) If the current sense multiplexer is set to Channel 0 to 3
- 5) The over current latch off flag is set latched and can be cleared by SPI command HWCR.CL
- 6) The over temperature flag is set latched and can be cleared by SPI command HWCR.CL

8.1 Diagnosis Word at SPI

The standard diagnosis at the SPI interface provides information about each channel. The error flags, an OR combination of the over temperature flags and the over load monitoring signals are provided in the SPI standard diagnosis bits ERRn.

The over load monitoring signals are latched in the error flags and cleared each time the standard diagnosis is transmitted via SPI. In detail, they are cleared between the second and third raising edge of the SCLK signal.

The over temperature flags, which cause an overheated channel to latch off, are latched directly at the gate control block. The over current flags, which cause an channel 0 or 1 driving a too high current to switch off, are latched like the over temperature flags. Those latches are cleared by SPI command HWCR.CL.

Please note: The over temperature and over current information is latched twice. When transmitting a clear latch command (HWCR.CL), the error flag is cleared during command transmission of the next SPI frame and ready for latching after the third raising edge of the SCLK signal. As a result, the first standard diagnosis information after a CL command will indicate a failure mode at the previously affected channels although the thermal latches have been cleared already. In case of continuous over load, the error flags are set again immediately because of the over load monitoring signal.



8.2 Load Current Sense Diagnosis

There is a current sense signal available at pin IS which provides a current proportional to the load current of one selected channel. The selection is done by a multiplexer which is configured via SPI.

Current Sense Signal

The current sense signal (ratio $k_{\rm ILIS} = I_{\rm L} / I_{\rm S}$) is provided during on-state as long as no failure mode occurs. The ratio $k_{\rm ILIS}$ can be adjusted to the load type (LED or bulb) via SPI register HWCR for channel 2 and 3. The accuracy of the ratio $k_{\rm ILIS}$ depends on the load current. Usually a resistor $R_{\rm IS}$ is connected to the current sense pin. It is recommended to use resistors 1.5 k Ω < $R_{\rm IS}$ < 5 k Ω . A typical value is 2.7 k Ω .

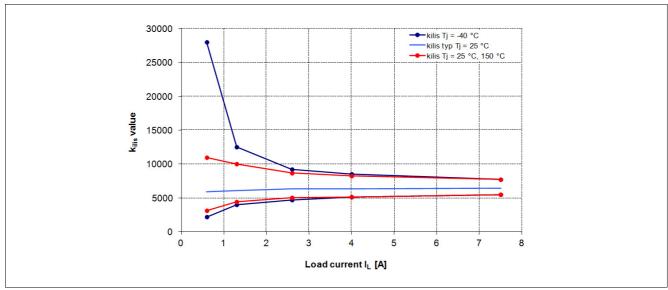


Figure 17 Current Sense Ratio $k_{\rm ILIS}$ Channel 0, 1 $^{1)}$

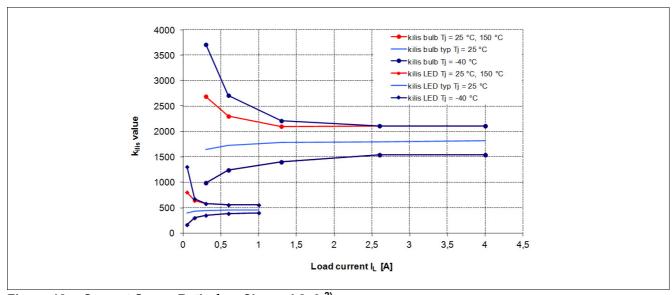


Figure 18 Current Sense Ratio $k_{\rm ILIS}$ Channel 2, 3 $^{2)}$

¹⁾ The curves show the behavior based on characterization data. The marked points are guaranteed in this Data Sheet in **Section 8.5** (Position **8.5.1**).

²⁾ The curves show the behavior based on characterization data. The marked points are guaranteed in this Data Sheet in **Section 8.5** (Position **8.5.1**).



In case of off-state, over current, dynamic temperature sensor shut down ($n < n_{\rm retry}$), dynamic temperature sensor latch ($n = n_{\rm retry}$) as well as over temperature, the current sense signal of the affected channel is switched off. To distinguish between over temperature or over current and over load, the SPI diagnosis word can be used. Whereas the over load and dynamic temperature sensor shut down ($n < n_{\rm retry}$) flag is cleared every time the diagnosis is transmitted. The over temperature, dynamic temperature sensor latch ($n = n_{\rm retry}$) and over current flag is cleared by a dedicated SPI command (HWCR.CL).

Details about timings between the current sense signal $I_{\rm IS}$ and the output voltage $V_{\rm OUT}$ and the load current $I_{\rm L}$ can be found in **Figure 19**.

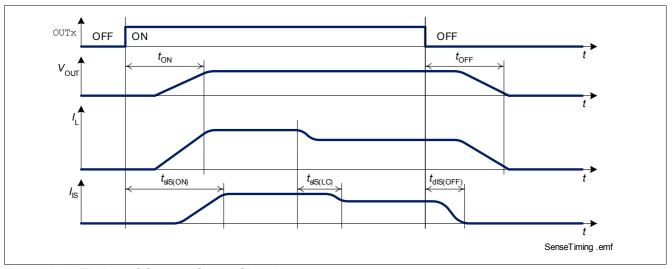


Figure 19 Timing of Current Sense Signal

Current Sense Multiplexer

There is a current sense multiplexer implemented in the SPOC - BTS5461SF that routes the sense current of the selected channel to the diagnosis pin IS. The channel is selected via SPI register DCR.MUX. The sense current also can be disabled by SPI register DCR.MUX. For details on timing of the current sense multiplexer, please refer to Figure 20.

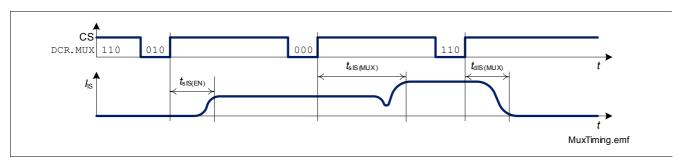


Figure 20 Timing of Current Sense Multiplexer



Current Sense Offset Trimming

To increase the current sense accuracy of SPOC - BTS5461SF, a circuitry to measure and trim the sense offset current is implemented. This so called calibration mode is activated by the SPI command $\mathtt{ICR.CAL} = 1_{b}$. In calibration mode, a current proportional to the positive offset of the operational amplifier is provided on the IS pin. To increase the accuracy of the calibration this current is amplified by a factor of 10 (typical value) when calibration mode is entered. The offset of the operational amplifier can be trimmed by 15 steps which are selected by the bits $\mathtt{KILIS.OSTn.}$ (see. Chapter 9.6 for detailed information). To exit the calibration mode $\mathtt{ICR.CAL}$ is set to 0_{b} . During calibration the state of the current sense multiplexer should not be changed, otherwise the measured current could be affected. If $\mathtt{DCR.MUX} = 111$ the device exits calibration mode and stand-by mode is entered. In general the calibration mode does not have any effect on other SPI registers or functions of the device. In case of calibration during operation switching transients on the supply line must be considered.

8.3 Switch Bypass Diagnosis

To detect short circuit to $V_{\rm S}$, there is a switch bypass monitor implemented. In case of short circuit between the output pin OUT and $V_{\rm S}$ in ON-state, the current will flow through the power transistor as well as through the short circuit (bypass) with undefined ratio. As a result, the current sense signal will show lower values than expected by the load current. In OFF-state, the output voltage will stay close to $V_{\rm S}$ potential which means a small $V_{\rm DS}$.

The switch bypass monitor compares the voltage $V_{\rm DS}$ across the power transistor of that channel, which is selected by the current sense multiplexer (DCR.MUX) with threshold $V_{\rm DS(SB)}$. The result of comparison can be read in SPI register DCR.SBM or in the standard diagnosis.

8.4 Open Load in OFF-State

For performing a dedicated open load in OFF-state detection a current source can be switched in parallel to the DMOS according to the Figure 16. The current source current can be programmed in two steps by the bit ICR.CSL.

The following procedure is recommended to use:

- Select the dedicated channel with the multiplexer
- Enable the open load current with the DCR.CSOL bit
- Read the DCR.SBM or the standard diagnosis
- Disable the open load current with the DCR.CSOL bit



Diagnosis

8.5 Electrical Characteristics

Electrical Characteristics Diagnosis

Pos.	Parameter	Symbol	Li	mit Valı	ıes	Unit	Test Conditions
			min.	typ.	max.		
Load	Current Sense	1					
8.5.1	Current sense ratio	k_{ILIS}					T _i = -40 °C
	channel 0, 1:						
	0.600 A		2190	5840	28000		_
	1.3 A		3990	6140	12510		_
	2.6 A		4690	6350	9210		_
	4.0 A		5130	6430	8510		_
	7.5 A		5490	6480	7710		_
	channel 2, 3 (bulb):						HWCR.LEDn = 0
	0.300 A		990	1670	3710		_
	0.600 A		1240	1750	2710		_
	1.3 A		1400	1800	2210		_
	2.6 A		1540	1830	2110		_
	4.0 A		1540	1840	2110		_
	channel 2, 3 (LED):						HWCR.LEDn = 1
	0.050 A		165	400	1305		_
	0.150 A		300	440	675		_
	0.300 A		350	450	580		_
	0.600 A		385	460	555		_
	1.0 A		400	500	555		-
8.5.2	Current sense ratio	k_{ILIS}					$T_{\rm j}$ = 25 °C to 150 °C
	channel 0, 1:						
	0.600 A		3120	5840	10960		_
	1.3 A		4420	6140	10010		_
	2.6 A		5030	6350	8660		_
	4.0 A		5130	6430	8240		_
	7.5 A		5490	6480	7710		_
	channel 2, 3 (bulb):						HWCR.LEDn = 0
	0.300 A		990	1670	2690		_
	0.600 A		1240	1750	2300		_
	1.3 A		1400	1800	2100		_
	2.6 A		1540	1830	2110		_
	4.0 A		1540	1840	2110		_
	channel 2, 3 (LED):						HWCR.LEDn = 1
	0.050 A		165	400	805		_
	0.150 A		300	440	640		_
	0.300 A		350	450	580		_
	0.600 A		385	460	555		_
	1.0 A		400	500	555		_



Diagnosis

Electrical Characteristics Diagnosis (cont'd)

Pos.	Parameter	Symbol	Liı	mit Va	lues	Unit	Test Conditions	
			min.	typ.	max.			
3.5.3	Current sense drift of unaffected channel	$\Delta k_{\rm ILIS(IC)}$					1)	
	during inverse current of other channels						DCR.MUX ≠ 111	
	channel 0, 1						$I_{L0, 1} = 7.5 \text{ A}$	
			-20 %		20 %		$I_{L1, 0 (IC)} = 7.5 A$	
			-20 %	_	20 %		$I_{L2, 3 (IC)} = 2.6 A$	
	channel 2, 3 (bulb)						HWCR.LEDn = 0	
			00.0/		00.0/		$I_{L2, 3} = 2.6 \text{ A}$	
			-20 %	_	20 %		$I_{\text{L0, 1 (IC)}} = 7.5 \text{ A}$	
	shannal 2, 2 (LED)		-20 %	_	20 %		$I_{L3, 2 (IC)} = 2.6 \text{ A}$	
	channel 2, 3 (LED)						HWCR.LEDn = 1	
			-20 %	_	20 %		$I_{L2, 3} = 0.6 \text{ A}$	
			-20 %		20 %		$I_{L0, 1 (IC)} = 7.5 A$	
) E 1	Calibration atom	ī	20 70		20 70		$I_{L3, 2 \text{ (IC)}} = 2.6 \text{ A}$	
3.5.4	Calibration step	$I_{IS(CAL)}$		7.5		μΑ	$T_{\rm j} = 25 ^{\circ}{\rm C}$ ICR.CAL = 0	
				7.5			ICR.CAL = 0	
3.5.5	Maximum steady state current sense	I	5.5	_	20	mA	$^{1)}V_{1S} = 0 \text{ V}$	
5.5.5	output current	$I_{\rm IS(MAX)}$	3.3		20	ША	V _{IS} – U V	
3.5.6	Current sense leakage / offset current	I				μA	I ₁ = 0 A	
5.5.0	ourient sense leakage / onset current	$I_{\rm IS(en)}$				μΛ	DCR.MUX ≠ 111	
	channel 0, 1		_	_	76		DCI(:11071 + 111	
	channel 2, 3		_	_	76			
8.5.7	Current sense leakage, while diagnosis	$I_{IS(dis)}$	_	_	1	μA	DCR.MUX = 110	
	disabled	10(019)				'		
8.5.8	Current sense settling time after channel	$t_{\sf sIS(ON)}$				μs	V _S = 13.5 V	
	activation	0.0(0.11)				ľ	$R_{\rm IS}$ = 2.7 k Ω	
	channel 0, 1		_	_	150		$R_{\rm L}$ = 2.2 Ω	
	channel 2, 3						HWCR.LEDn = 0	
			_	_	150		$R_{\rm L}$ = 6.8 Ω	
							HWCR.LEDn = 1	
			_	_	100		$R_{\rm L}$ = 33 Ω	
3.5.9	Current sense desettling time after	$t_{\sf dIS(OFF)}$				μs	$^{1)} V_{\rm S}$ = 13.5 V	
	channel deactivation						$R_{\rm IS}$ = 2.7 k Ω	
			_	_	25		HWCR.LEDn = 0	
			_	-	25		HWCR.LEDn = 1	
3.5.10		$t_{\rm sIS(LC)}$				μs	$^{1)}V_{\rm S}$ = 13.5 V	
	of load current						$R_{\rm IS}$ = 2.7 k Ω	
	channel 0, 1		_	-	30		$I_{\rm L}$ = 7.5 A to 4.0 A	
	channel 2, 3						HWCR.LEDn = 0	
			-	-	30		$I_{\rm L}$ = 2.6 A to 1.3 A	
							HWCR.LEDn = 1	
			-	-	30		$I_{\rm L}$ = 0.6 A to 0.3 A	



Diagnosis

Electrical Characteristics Diagnosis (cont'd)

Pos.	Parameter	Symbol	L	imit Va	lues	Unit	Unit Test Conditions		
			min.	typ.	max.				
8.5.11	Current sense settling time after current sense activation	t _{sIS(EN)}	_	_	25	μs	$R_{\rm IS}$ = 2.7 k Ω DCR.MUX: 110 -> 000		
8.5.12	Current sense settling time after multiplexer channel change	$t_{\sf sIS(MUX)}$	_	_	30	μs	$R_{\rm IS} = 2.7 \rm k\Omega$ $R_{\rm L0} = 2.2 \Omega$ $R_{\rm L2} = 33 \Omega$ DCR.MUX: 010 -> 000		
8.5.13	Current sense deactivation time	$t_{dIS(MUX)}$	_	_	25	μs	¹⁾ R_{IS} = 2.7 kΩ DCR.MUX: 000 -> 110		
Switc	h Bypass Monitor								
8.5.14	Switch bypass monitor threshold	$V_{DS(SB)}$	1.5	_	4	V	_		
Open	load in off current source	, , ,		"	,				
8.5.15	Current source in OFF-state	$I_{L(OL)}$	100 3.0		450 7.5	μA mA	<pre>ICR.CSL = 0 ICR.CSL = 1</pre>		

¹⁾ Not subject to production test, specified by design.



9 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) is a full duplex synchronous serial slave interface, which uses four lines: \underline{SO} , \underline{SI} , \underline{SCLK} and \underline{CS} . Data is transferred by the lines \underline{SI} and \underline{SO} at the rate given by \underline{SCLK} . The falling edge of \underline{CS} indicates the beginning of an access. Data is sampled in on line \underline{SI} at the falling edge of \underline{SCLK} and shifted out on line \underline{SO} at the rising edge of \underline{SCLK} . Each access must be terminated by a rising edge of \underline{CS} . A modulo 8 counter ensures that data is taken only, when a multiple of 8 bit has been transferred. The interface provides daisy chain capability.

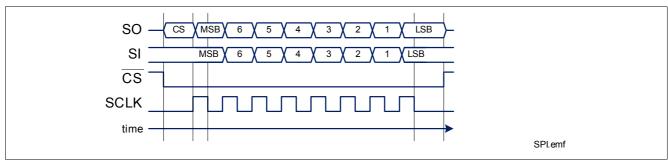


Figure 21 Serial Peripheral Interface

9.1 SPI Signal Description

CS - Chip Select:

The system micro controller selects the SPOC - BTS5461SF by means of the \overline{CS} pin. Whenever the pin is in low state, data transfer can take place. When \overline{CS} is in high state, any signals at the SCLK and SI pins are ignored and SO is forced into a high impedance state.

CS High to Low transition:

- The requested information is transferred into the shift register.
- SO changes from high impedance state to high or low state depending on the logic OR combination between
 the transmission error flag (TER) and the signal level at pin SI. As a result, even in daisy chain configuration,
 a high signal indicates a faulty transmission. This information stays available to the first rising edge of SCLK.

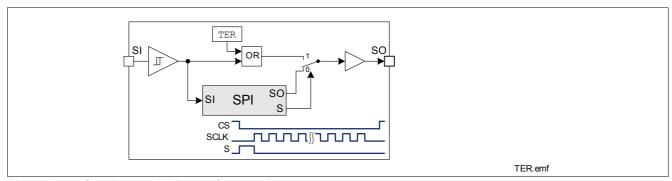


Figure 22 Combinatorial Logic for TER Flag

CS Low to High transition:

- Command decoding is only done, when after the falling edge of \overline{CS} exactly a multiple (1, 2, 3, ...) of eight SCLK signals have been detected. In case of faulty transmission, the transmission error flag (TER) is set and the command is ignored.
- · Data from shift register is transferred into the addressed register.



SCLK - Serial Clock:

This input pin clocks the internal shift register. The serial input (SI) transfers data into the shift register on the falling edge of SCLK while the serial output (SO) shifts diagnostic information out on the rising edge of the serial clock. It is essential that the SCLK pin is in low state whenever chip select $\overline{\text{CS}}$ makes any transition.

SI - Serial Input:

Serial input data bits are shift-in at this pin, the most significant bit first. SI information is read on the falling edge of SCLK. The input data consists of two parts, control bits followed by data bits. Please refer to **Section 9.5** for further information.

SO Serial Output:

Data is shifted out serially at this pin, the most significant bit first. SO is in high impedance state until the CS pin goes to low state. New data will appear at the SO pin following the rising edge of SCLK. Please refer to **Section 9.5** for further information.

9.2 Daisy Chain Capability

The SPI of SPOC - BTS5461SF provides daisy chain capability. In this configuration several devices are activated by the same $\overline{\text{CS}}$ signal $\overline{\text{MCS}}$. The SI line of one device is connected with the SO line of another device (see Figure 23), in order to build a chain. The ends of the chain are connected with the output and input of the master device, MO and MI respectively. The master device provides the master clock MCLK which is connected to the SCLK line of each device in the chain.

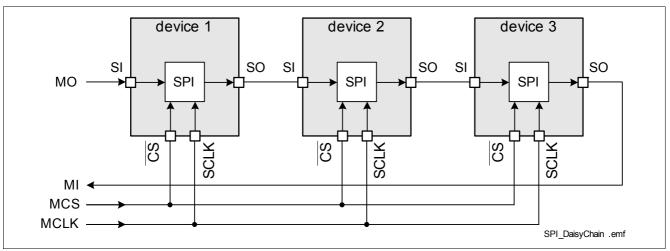


Figure 23 Daisy Chain Configuration

In the SPI block of each device, there is one shift register where one bit from SI line is shifted in each SCLK. The bit shifted out occurs at the SO $\underline{\text{pin}}$. After eight SCLK cycles, the data transfer for one device has been finished. In single chip configuration, the $\overline{\text{CS}}$ line must turn high to make the device accept the transferred data. In daisy chain configuration, the data shifted out at device 1 has been shifted in to device 2. When using three devices in daisy chain, three times eight bits have to be shifted through the devices. After that, the $\overline{\text{MCS}}$ line must turn high (see Figure 24).

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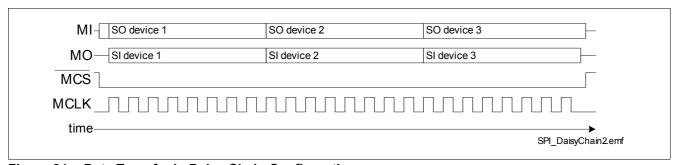


Figure 24 Data Transfer in Daisy Chain Configuration

9.3 Timing Diagrams

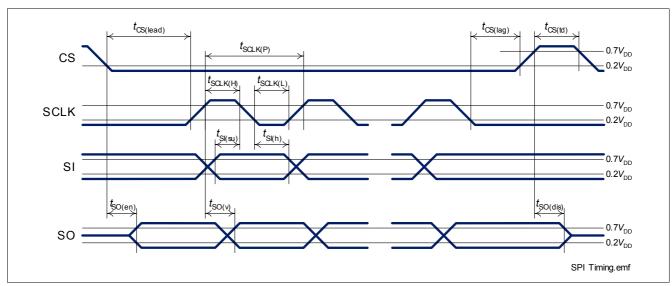


Figure 25 Timing Diagram SPI Access

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Electrical Characteristics 9.4

Electrical Characteristics Serial Peripheral Interface (SPI)

Pos.	Parameter	Symbol	Lir	nit Val	lues	Unit	Test Conditions	
			min.	typ.	max.			
nput	Characteristics (CS, SCLK, SI)	1						
).4.1	L level of pin CS SCLK SI	$V_{\rm SCLK(L)}$	0	_	0.2* V _{DD}	V	V _{DD} = 4.3 V	
4.2	H level of pin CS SCLK	$V_{\mathrm{CS(H)}} \ V_{\mathrm{SCLK(H)}}$	0.4* V _{DD}	_	V_{DD}	V	V _{DD} = 4.3 V	
.4.3	Pull-up resistor at CS pin	R_{CS}	50	120	180	kΩ	$I_{\rm CS}$ = 100 $\mu {\rm A}$	
.4.4		$R_{ m SCLK} \ R_{ m SI}$	50	120	180	kΩ	$I_{\rm SCLK}$ = 100 μ A $I_{\rm SI}$ = 100 μ A	
utpı	ut Characteristics (SO)							
9.4.5	L level output voltage	$V_{\mathrm{SO(L)}}$	0	_	0.4	V	$I_{\rm SO}$ = -0.5 mA	
4.6	H level output voltage	$V_{\rm SO(H)}$	V _{DD} - 0.4 V	_	V_{DD}	V	I_{SO} = 0.5 mA V_{DD} = 4.3 V	
.4.7	Output tristate leakage current	$I_{\rm SO(OFF)}$	-10	_	10	μΑ	$V_{\rm CS} = V_{\rm DD}$	
min	gs			-11	1			
4.8	Serial clock frequency	$f_{\sf SCLK}$	0		5 3	MHz	$^{1)}$ $V_{\rm DD}$ = 4.3 V $^{2)}$ $V_{\rm DD}$ = 3.0 V	
4.9	Serial clock period	t _{SCLK(P)}	200 333	_		ns	¹⁾ $V_{\rm DD}$ = 4.3 V ²⁾ $V_{\rm DD}$ = 3.0 V	
4.10	Serial clock high time	t _{SCLK(H)}	100 166	- -	_ _	ns	$^{1)}$ $V_{\rm DD}$ = 4.3 V $^{2)}$ $V_{\rm DD}$ = 3.0 V	
).4.11	Serial clock low time	$t_{SCLK(L)}$	100 166	_ _	_ _	ns	$^{1)}$ $V_{\rm DD}$ = 4.3 V $^{2)}$ $V_{\rm DD}$ = 3.0 V	
9.4.12	Enable lead time (falling $\overline{\text{CS}}$ to rising SCLK)	$t_{\mathrm{CS(lead)}}$	200 333	_ _	_	ns	$^{1)}$ $V_{\rm DD}$ = 4.3 V $^{2)}$ $V_{\rm DD}$ = 3.0 V	
9.4.13	Enable lag time (falling SCLK to rising $\overline{\text{CS}}$)	$t_{\rm CS(lag)}$	200 333	_ _	_	ns	$^{1)}$ $V_{\rm DD}$ = 4.3 V $^{2)}$ $V_{\rm DD}$ = 3.0 V	
9.4.14	Transfer delay time (rising $\overline{\text{CS}}$ to falling $\overline{\text{CS}}$)	$t_{\rm CS(td)}$	200 333	_ _		ns	¹⁾ $V_{\rm DD}$ = 4.3 V ²⁾ $V_{\rm DD}$ = 3.0 V	
9.4.15	Data setup time (required time SI to falling SCLK)	$t_{\rm SI(su)}$	20 33	_ _		ns	$^{1)}$ $V_{\rm DD}$ = 4.3 V $^{2)}$ $V_{\rm DD}$ = 3.0 V	
9.4.16	Data hold time (falling SCLK to SI)	t _{SI(h)}	20 33	_	_	ns	¹⁾ $V_{\rm DD}$ = 4.3 V ²⁾ $V_{\rm DD}$ = 3.0 V	



Electrical Characteristics Serial Peripheral Interface (SPI) (cont'd)

Unless otherwise specified: $V_{\rm S}$ = 8 V to 17 V, $V_{\rm DD}$ = 3.0 V to 5.5 V, $T_{\rm j}$ = -40 °C to +150 °C typical values: $V_{\rm S}$ = 13.5 V, $V_{\rm DD}$ = 4.3 V, $T_{\rm j}$ = 25 °C

Pos.	Parameter	Symbol	Li	mit Val	ues	Unit	Test Conditions	
			min.	typ.	max.			
9.4.17	Output enable time (falling CS to SO	$t_{\rm SO(en)}$				ns	$^{2)} C_{L} = 20 \text{ pF}$	
	valid)	,	_	_	200		$V_{\rm DD}$ = 4.3 V	
			_	_	333		$V_{\rm DD}$ = 3.0 V	
9.4.18	Output disable time (rising CS to SO	$t_{\rm SO(dis)}$				ns	$^{2)} C_{L} = 20 \text{ pF}$	
	tri-state)	()	_	_	200		$V_{\rm DD} = 4.3 \text{ V}$	
			_	_	333		$V_{\rm DD}$ = 3.0 V	
9.4.19	Output data valid time with capacitive	$t_{\rm SO(v)}$				ns	$^{2)} C_{L} = 20 \text{ pF}$	
	load		_	_	100		$V_{\rm DD} = 4.3 \rm V$	
			_	_	166		V_{DD} = 3.0 V	

¹⁾ Not subject to production test, specified by design. SPI functional test is performed at $f_{\rm SCLK}$ = 5 MHz.

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²⁾ Not subject to production test, specified by design.



9.5 SPI Protocol 8 Bit

	CS ¹⁾	7	6	5	4	3	2	1	0		
	Write OUTL and KILIS Register										
SI		1	0	AD	DR		DATA				
		Read OUTL	and KILIS	Register							
SI		0	0	AD	DR	х	Х	Х	0		
	Write Configuration and Control Registers										
SI		1	1	AD	DR		DATA				
		Read Config	guration and	Control Re	gisters						
SI		0	1	AD	DR	х	Х	Х	0		
		Read Stand	ard Diagnos	sis							
SI		0	Х	х	Х	х	х	х	1		
		Standard Di	agnosis								
SO	TER	0	LHI	SBM	Х	ERR3	ERR2	ERR1	ERR0		
		Second Frame of Read Command									
SO	TER	1	0	0	0	OUT3	OUT2	OUT1	OUT0		
SO	TER	1	1	ADDR DATA							

¹⁾ The SO pin shows this information between $\overline{\text{CS}}$ hi -> lo and first SCLK lo -> hi transition.

Note: Reading a register needs two SPI frames. In the first frame the RD command is sent. In the second frame the output at SPI signal SO will contain the requested information. A new command can be executed in the second frame. The standard diagnosis can be accessed either by sending the standard diagnosis read command or it is transmitted after each write command.

Field	Bits	Type	Description
W/R	7	W	0 Read
			1 Write
RB	6	r	Register Bank
			Read / write to OUTL and KILIS register
			1 Read / write to the other register
TER	CS	r	Transmission Error
			Previous transmission was successful (modulo 8 clocks received)
			1 Previous transmission failed or first transmission after reset
ADDR	6:5	rw	Address
			Pointer to register for read and write command
DATA	4:0	rw	Data
			Data written to or read from register selected by address ADDR
ERRn	n	r	Diagnosis of Channel n
n = 3 to 0			0 No failure
			1 Over temperature, over current, over load or short circuit for
			channel 0 to 3
SBM	5	r	Switch Bypass Monitor 1)
			$0 V_{\rm DS} < V_{\rm DS(SB)}$
			1 $V_{\rm DS} > V_{\rm DS(SB)}$



Field	Bits	Type	Description
OUTn	n	r	Output Status for Channel n
n = 3 to 0			Channel is switched off
			1 Channel is switched on
LHI	6	r	Limp Home Enable ²⁾
			0 H-input signal at LHI pin
			1 L-input signal at LHI pin

¹⁾ Invalid in stand-by mode

9.6 Register Overview

RB	Address N		Name	Description			
0	0	0	OUTL	Output Configuration Register Low			
0	1	0	KILIS	Current Sense Offset Calibration Register			
1	0	1	ICR	Input and Current Source Configuration Register			
1	1	0	HWCR	Hardware Configuration Register			
1	1	1	DCR	Diagnosis Control Register			

Bit	7	6	5	4	3	2	1	0	
Name	W/R	RB	ΑC	DR		default 1)			
OUTL	W/R	0	0	0	OUT3	OUT2	OUT1	OUT0	00 _H
KILIS	W/R	0	1	0	OST3	OST2	OST1	OST0	28 _H
ICR	W/R	1	0	1	COL	INCG	CSL	CAL	00 _H
HWCR	R	1	1	0	LED3	LED2	STB	CL	02 _H
	W	1	1	0	LED3	LED2	RST	CL	-
DCR	R	1	1	1	SBM		MUX	1	07 _H
	W	1	1	1	CSOL		MUX		-

¹⁾ The default values are set after reset.

Note: A readout of an unused register will return the standard diagnosis.

²⁾ Not latching information, read of LHI-status during falling CS



Field	Bits	Type	Description
OUTL	n	rw	Output Control Register for Channel 0 to 3
n = 3 to 0			0 OFF
			1 ON
OSTn	n	rw	IS Offset Trimming
n = 3 to 0			$I_{\rm IS(EN)}$ - 8 x $I_{\rm IS(CAL)}$
			0001 $I_{IS(EN)}$ - 7 x $I_{IS(CAL)}$
			0010 $I_{IS(EN)}$ - 6 x $I_{IS(CAL)}$
			0011 $I_{IS(EN)}$ - 5 x $I_{IS(CAL)}$
			0100 $I_{IS(EN)}$ - 4 x $I_{IS(CAL)}$
			0101 $I_{IS(EN)}$ - 3 x $I_{IS(CAL)}$
			0110 $I_{IS(EN)}$ - 2 x $I_{IS(CAL)}$
			0111 $I_{IS(EN)}$ - 1 x $I_{IS(CAL)}$
			1000 $I_{\text{IS(EN)}}$ without Offset calibration
			1001 $I_{IS(EN)}$ + 1 x $I_{IS(CAL)}$
			$1010 I_{IS(EN)} + 2 \times I_{IS(CAL)}$
			$1011 I_{IS(EN)} + 3 \times I_{IS(CAL)}$
			$I_{\rm IS(EN)} + 4x I_{\rm IS(CAL)}$
			$1101 I_{IS(EN)} + 5 \times I_{IS(CAL)}$
			$I_{\text{IS}(\text{EN})} + 6 \times I_{\text{IS}(\text{CAL})}$
			1111 $I_{\text{IS(EN)}}$ + 7 x $I_{\text{IS(CAL)}}$
CAL	0	rw	IS Offset Calibration
			Calibration mode is deactivated
			1 Calibration mode is activated
CSL	1	rw	Level for Current Source for Open Load Detection
			0 Low level
			1 High level
INCG	2	rw	Input Drive Configuration
			O Direct drive mode
			1 Assigned drive mode
COL	3	rw	Input Combinatorial Logic Configuration
			Input signal OR-combined with according OUTL register bit
	_		1 Input signal AND-combined with according OUTL register bit
STB	1	r	Standby Mode
			0 Device is awake
			1 Device is in Standby mode
LEDn	n	rw	Set LED Mode for Channel n
n = 3 to 2			O Channel n is in bulb mode
			1 Channel n is in LED mode
CL	0	rw	Clear Latch
			Thermal and over current latches are untouched
-			1 Command: Clear all thermal and over current latches
RST	1	w	Reset Command
			0 Normal operation
			1 Execute reset command



Field	Bits	Type	Description
MUX	2:0	rw	Set Current Sense Multiplexer Configuration in OFF-state
			000 IS pin is high impedance
			001 IS pin is high impedance
			010 IS pin is high impedance
			011 IS pin is high impedance
			100 IS pin is high impedance
			101 IS pin is high impedance
			110 IS pin is high impedance
			111 Stand-by mode (IS pin is high impedance)
			Set Multiplexer Configuration in ON-state
			000 Current sense of channel 0 is routed to IS pin
			001 Current sense of channel 1 is routed to IS pin
			010 Current sense of channel 2 is routed to IS pin
			011 Current sense of channel 3 is routed to IS pin
			100 IS pin is high impedance
			101 IS pin is high impedance
			110 IS pin is high impedance
			111 Stand-by mode (IS pin is high impedance))
SBM	3	r	Switch Bypass Monitor 1)
			$0 V_{\rm DS} < V_{\rm DS(SB)}$
			$1 V_{\rm DS} > V_{\rm DS(SB)}$
CSOL	3	w	Current Source Switch for Open Load Detection
			0 OFF
			1 ON

¹⁾ Invalid in stand-by mode



Application Description

10 Application Description

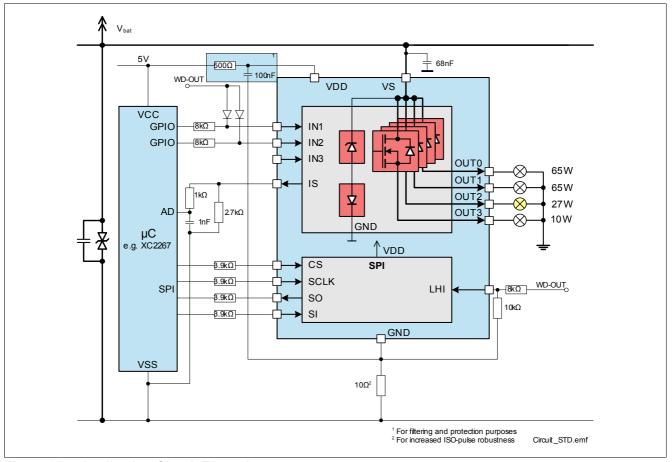


Figure 26 Application Circuit Example



Package Outlines SPOC - BTS5461SF

11 Package Outlines SPOC - BTS5461SF

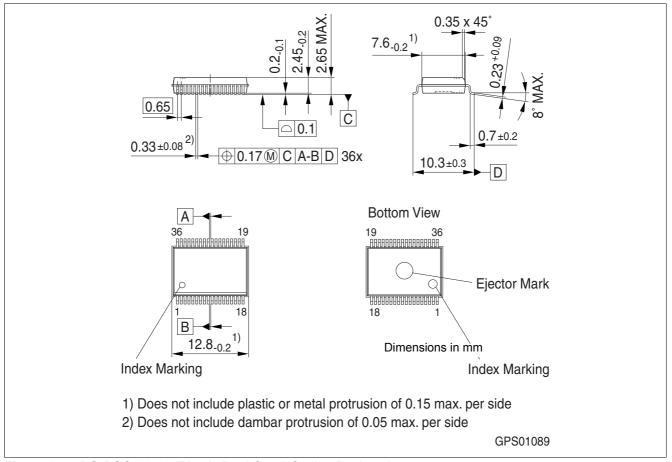


Figure 27 PG-DSO-36-43 (Plastic Dual Small Outline Package)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).



Revision History

12 Revision History

Revision	Date	Changes
1.0	2011-11-17	Initial revision

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